



ITW

PATENT
1630-0135P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Johngeon SHIN Conf.: 9721
Appl. No.: 10/765,100 Group: 2818
Filed: January 28, 2004 Examiner: TRAN, M.
For: CRYSTAL GROWTH METHOD OF NITRIDE
SEMICONDUCTOR

LARGE ENTITY TRANSMITTAL FORM

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

April 29, 2005

Sir:

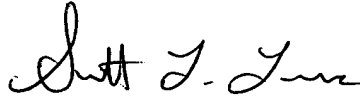
Transmitted herewith is a Reply to Restriction/Election Requirement in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ Petition for _____ () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ A check in the amount of \$0.00 is enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. A triplicate copy of this sheet is attached.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

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1630-0135P

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Attachment(s)

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REPLY TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

April 29, 2005

Sir:

In reply to the Restriction Requirement dated March 29, 2005, the following remarks are respectfully submitted in connection with the above-identified application.

This reply includes: Remarks.